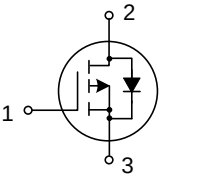
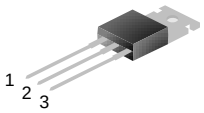
-12A, -55V P-CHANNEL MOSFET

GENERAL DESCRIPTION

SVD9Z24NT is a P-channel enhancement mode power MOS field effect transistor which is produced using Silan planar VDMOS process. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. This device is widely used in push-pull amplifier, high-side switching circuit, CMOS power amplifier.



1.Gate 2.Drain 3.Source



TO-220-3L

FEATURES

- -12A, -55V ,$R_{DS(on)(typ.)}$<175mΩ@V_{GS}=-10V
- P channel
- Low gate charge
- Low Crss
- Fast switching
- Improved dv/dt capability

ORDERING INFORMATION

Part No.	Package	Marking	Harzardous Substance Control	Packing Type
SVD9Z24NT	TO-220-3L	SVD9Z24N	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	-55	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current	T_C=25°C	I_D	-12	A
	T_C=100°C		-8.5	
Drain Current Pulsed		I_{DM}	-48	A
Power Dissipation(T_C=25°C)		P_D	45	W
-Derate above 25°C			0.36	W/°C
Single Pulsed Avalanche Energy (Note 1)		E_{AS}	106	mJ
Operation Junction Temperature Range		T_J	-55～+175	°C
Storage Temperature Range		T_{stg}	-55～+175	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.78	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250μA	-55	--	--	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-55V, V_{GS}=0V	--	--	-25	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=-250μA	-2.0	--	-4.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-7.2A	--	--	175	mΩ
Input Capacitance	C_{iss}	V_{DS}=-25V, V_{GS}=0V, f=1.0MHz	--	447	--	pF
Output Capacitance	C_{oss}		--	135	--	
Reverse Transfer Capacitance	C_{rss}		--	30	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-28V,V_{GS}=-10V, R_G=24Ω,I_D=-7.2A (Note 2,3)	--	8.47	--	ns
Turn-on Rise Time	t_r		--	41.2	--	
Turn-off Delay Time	$t_{d(off)}$		--	30	--	
Turn-off Fall Time	t_f		--	20.2	--	
Total Gate Charge	Q_g	V_{DS}=-44V,V_{GS}=-10V, I_D=-7.2A (Note 2,3)	--	13	--	nC
Gate-Source Charge	Q_{gs}		--	3.25	--	
Gate-Drain Charge	Q_{gd}		--	5.3	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	-12	A
Pulsed Source Current	I_{SM}		--	--	-48	
Diode Forward Voltage	V_{SD}	I_S=-7.2A, V_{GS}=0V	--	--	-1.6	V
Reverse Recovery Time	T_{rr}	I_S=-7.2A, V_{GS}=0V, dI_F/dt=100A/μs (Note 2)	--	50.5	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.11	--	μC

Notes:

1. L=3.7mH, I_{AS}= -8A, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs,Duty cycle≤2%;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

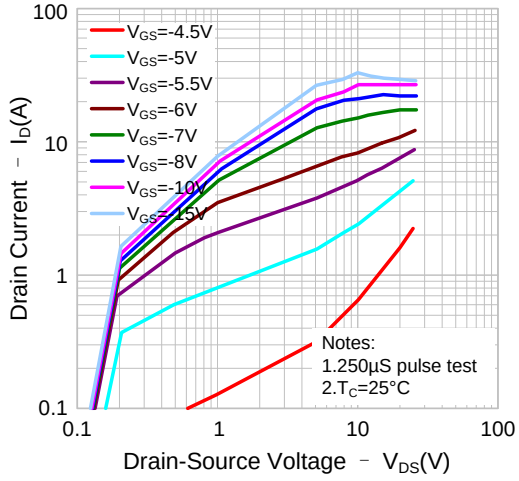


Figure 2. Transfer Characteristics

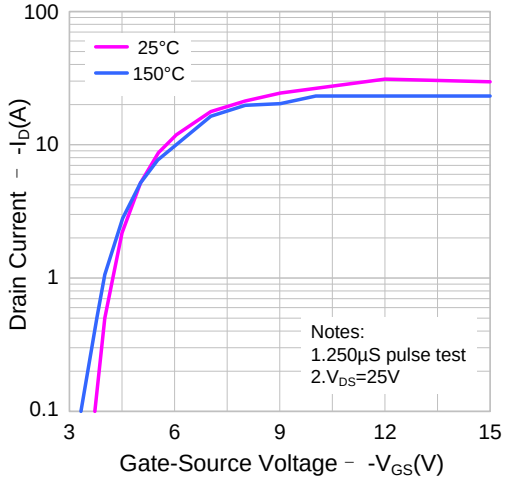


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

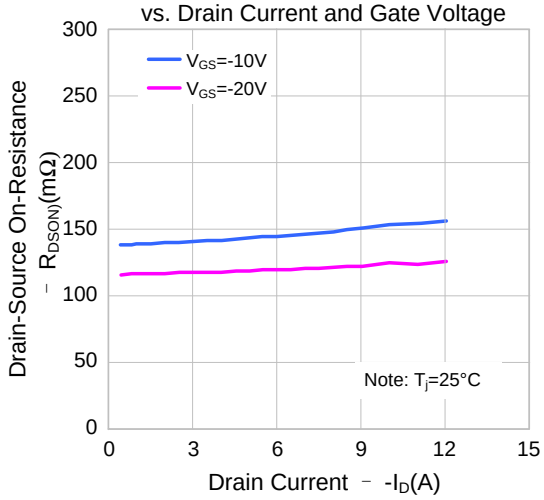


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

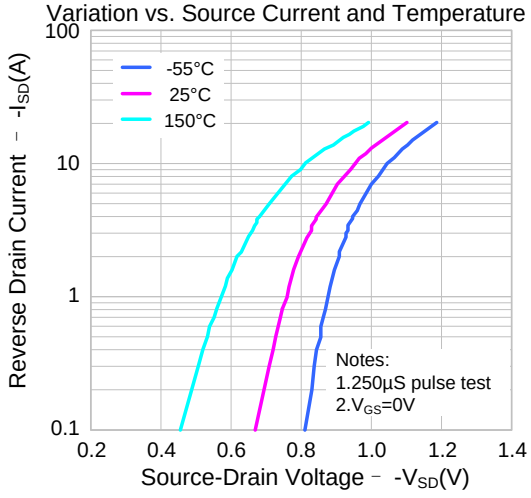


Figure 5. Capacitance Characteristics

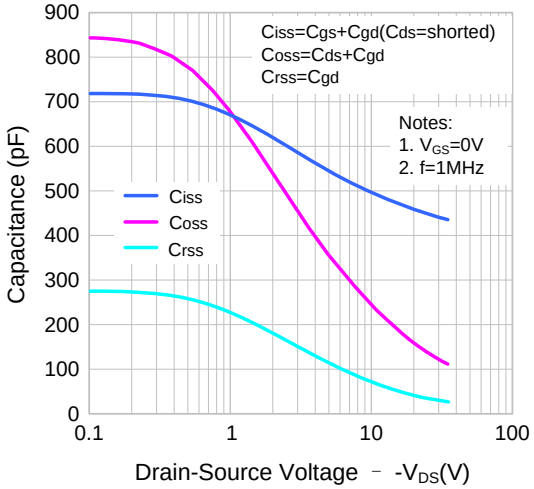
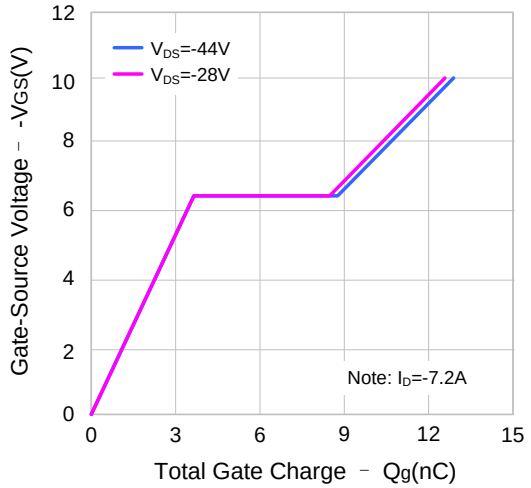


Figure 6. Gate Charge Characteristics



TYPICAL CHARACTERISTICS (CONTINUED)

Figure 7. Breakdown Voltage Variation vs. Temperature

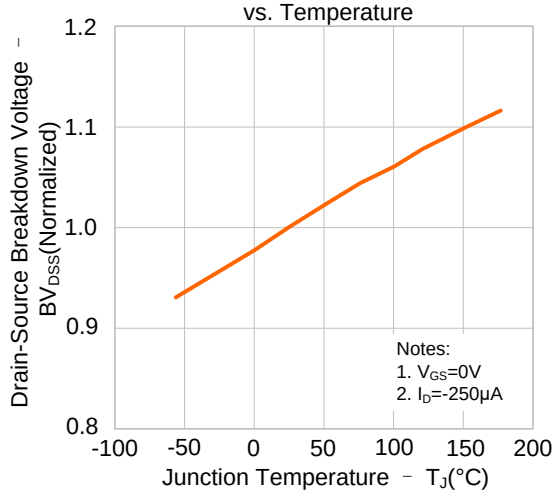


Figure 8. On-resistance Variation vs. Temperature

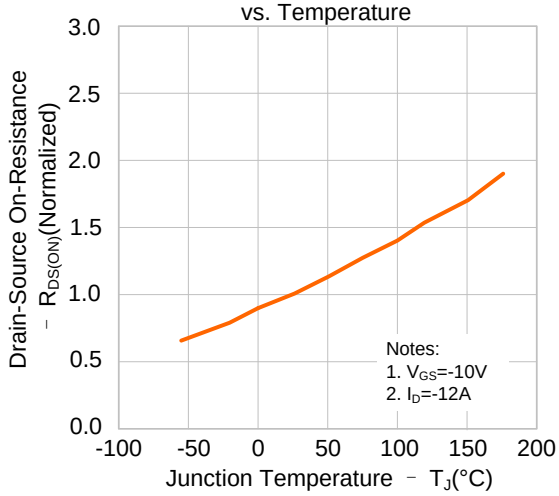


Figure 9. Max. Safe Operating Area

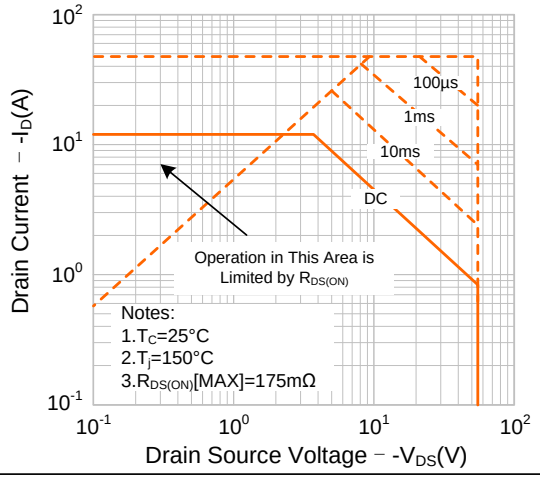
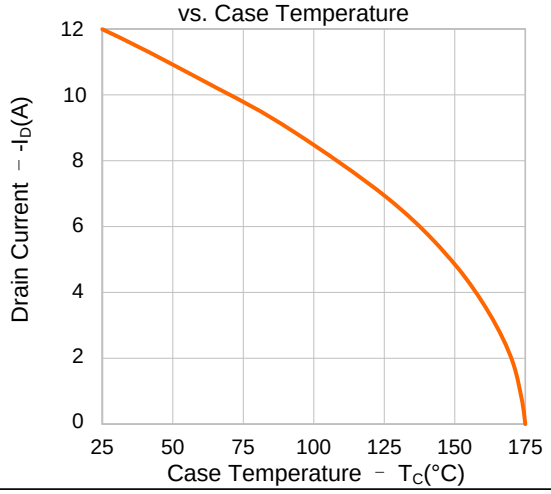
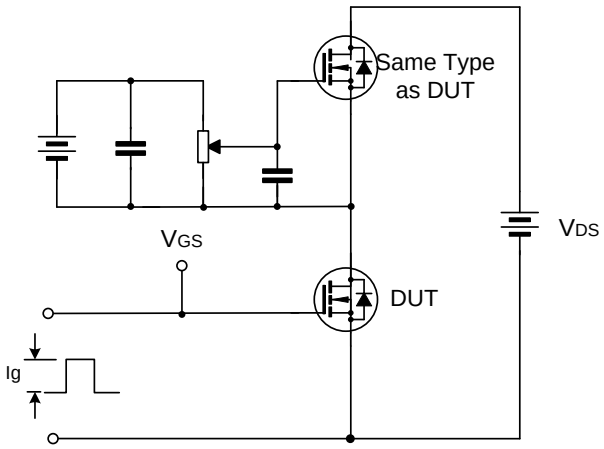


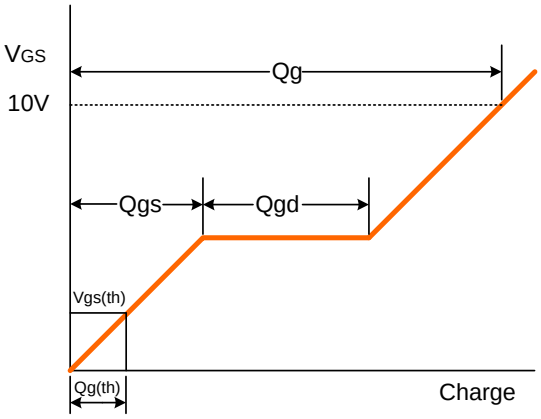
Figure 10. Maximum Drain Current vs. Case Temperature



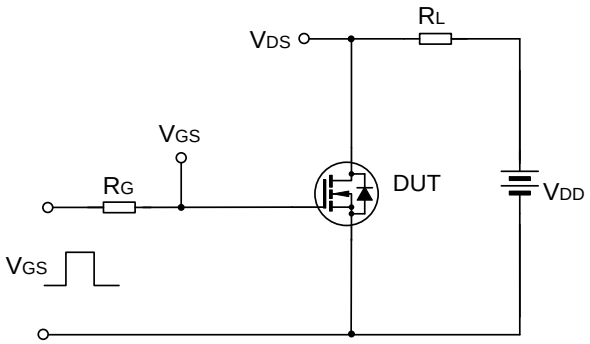
TYPICAL TEST CIRCUIT

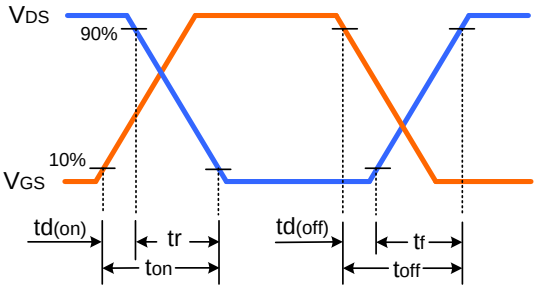
Gate Charge Test Circuit & Waveform



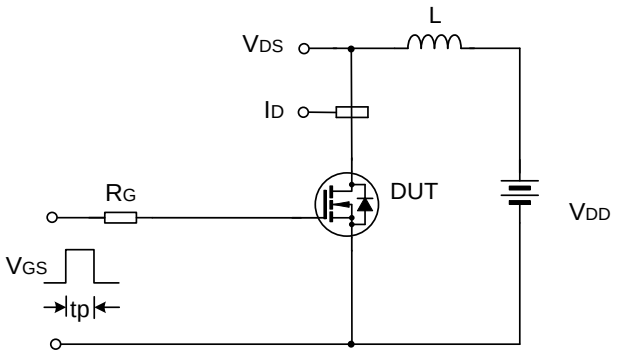


Resistive Switching Test Circuit & Waveform

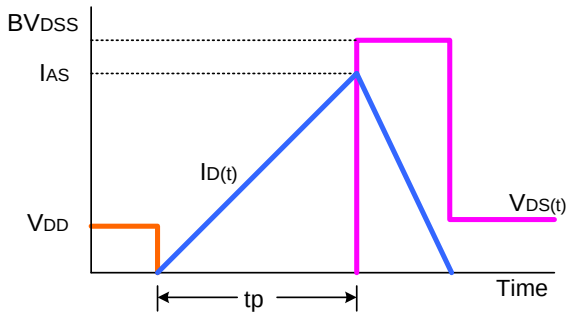




Unclamped Inductive Switching Test Circuit & Waveform

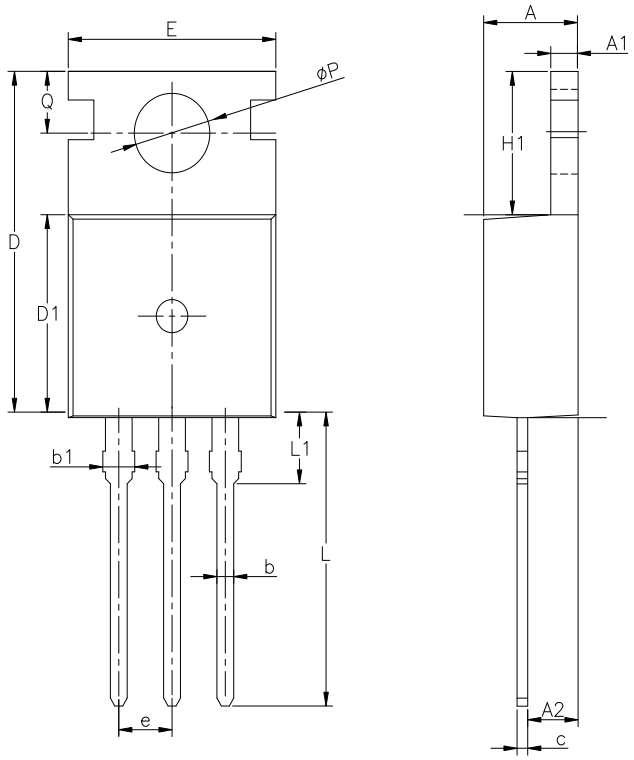


$$E_{AS} = \frac{1}{2} LI_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



PACKAGE OUTLINE

TO-220-3L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.00	1.30	1.50
A2	1.80	2.40	2.80
b	0.60	0.80	1.00
b1	1.00	—	1.60
c	0.30	—	0.70
D	15.10	15.70	16.10
D1	8.10	9.20	10.00
E	9.60	9.90	10.40
e	2.54BSC		
H1	6.10	6.50	7.00
L	12.60	13.08	13.60
L1	—	—	3.95
ϕP	3.40	3.70	3.90
Q	2.60	—	3.20

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Rev.: 1.4

Revision History:

1. Modify marketing
2. Modify the template of datasheet

Rev.: 1.3

Revision History:

1. Modify V_{GS} to -10V
2. Modify the Electrical diagram
3. Modify Fig 1
4. Modify TYPICAL TEST CIRCUIT（take the Chinese version as the standard）

Rev.: 1.2

Revision History:

1. Modify the
2. Modify the source-drain diode ratings and characteristics
3. Modify the electrical characteristics

Rev.: 1.1

Revision History:

1. Modify the package information of TO-220-3L

Rev.: 1.0

Revision History:

1. First release